

TMBYV 10-60

SMALL SIGNAL SCHOTTKY DIODE

DESCRIPTION

Metal to silicon rectifier diode in glass case featuring very low forward voltage drop and fast recovery time, intended for low voltage switching mode power supply, polarity protection and high frequency circuits.



ABSOLUTE MAXIMUM RATINGS (limiting values)

Symbol	Parameter	Value	Unit		
V _{RRM}	Repetitive Peak Reverse Voltage	60	V		
I _{F (AV)}	Average Forward Current	1	Α		
I _{FSM}	Surge non Repetitive Forward Current	ge non Repetitive Forward Current $T_i = 25 \ ^{\circ}C \\ t_p = 10 ms$		А	
		$\begin{array}{l} T_i = 25 \ ^\circ C \\ t_p = 300 \mu s \end{array}$	40 Rectangular Pulse		
T _{stg} Tj	Storage and Junction Temperature Range	- 65 to + 150 - 65 to + 125	°C °C		
TL	Maximum Lead Temperature for Soldering duri	260	°C		

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
R _{th (j} - I)	Junction-leads	110	°C/W

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol	Test Conditions			Тур.	Max.	Unit
I _R *	$T_j = 25^{\circ}C$	$V_{R} = V_{RRM}$			0.5	mA
	T _j = 100°C				10	117.
V _F *	I _F = 1A	$T_j = 25^{\circ}C$			0.7	V
	I _F = 3A				1	

* Pulse test: $t_p \leq 300 \mu s \ \delta < 2\%$.

DYNAMIC CHARACTERISTICS

;	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
	С	$T_j = 25^{\circ}C$ $V_R = 0$		150		pF
		$T_j = 25^{\circ}C$ $V_R = 5V$		40		

Forward current flow in a Schottky rectifier is due to majority carrier conduction. So reverse recovery is not affected by storage charge as in conventional PN junction diodes.

Nevertheless, when the device switches from forward biased condition to reverse blocking state, current is required to charge the depletion capacitance of the diode. This current depends only of diode capacitance and external circuit impedance. Satisfactory circuit behaviour analysis may be performed assuming that Schottky rectifier consists of an ideal diode in parallel with a variable capacitance equal to the junction capacitance (see fig. 5 page 4/4).

Figure 1. Forward current versus forward voltage at low level (typical values).



Figure 2. Forward current versus forward voltage at high level (typical values).



Figure 3. Reverse current versus junction temperature.



Figure 4. Reverse current versus V_{RRM} in per cent.



Figure 5. Capacitance C versus reverse applied voltage V_R (typical values)



Figure 6. Surge non repetitive forward current for a rectangular pulse with t \leq 10 ms.



Figure 7. Surge non repetitive forward current versus number of cycles.





PACKAGE MECHANICAL DATA

MELF Glass



	DIMENSIONS					
REF.	Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.
А	4.80		5.20	0.189		0.205
ØВ	2.50		2.65	0.098		0.104
С	0.45		0.60	0.018		0.024
ØD		2.50			0.098	

FOOT PRINT DIMENSIONS (Millimeter)



Marking: ring at cathode end. Weight: 0.15g

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